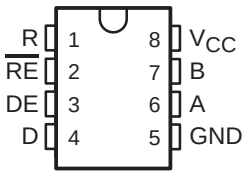
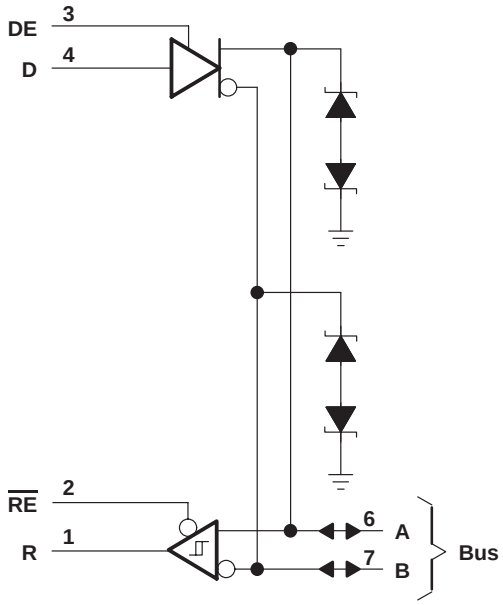
- **Integrated Transient Voltage Suppression**
- **ESD Protection for Bus Terminals:**
  - **– ±15 kV Human Body Model**
  - **– ±8 kV IEC1000-4-2, Contact Discharge**
  - **– ±15 kV IEC1000-4-2, Air-Gap Discharge**
- **Circuit Damage Protection of 400 W Peak (Typical)**
- **Controlled Driver Output-Voltage Slew Rates Allows Longer Cable Stub Lengths**
- **250-kbits/s in Electrically Noisy Environments**
- **Open-Circuit Fail-Safe Receiver Design**
- **1/2 Unit Load Allows for 64 Devices Connected on Bus**
- **Thermal Shutdown Protection**
- **Power-Up/-Down Glitch Protection**
- **Each Transceiver Meets or Exceeds the Requirements of EIA RS-485 and ISO/IEC 8482:1993(E) Standards**
- **Low Disabled Supply Current 300 μA Max**
- **Pin Compatible with SN75176**

D OR P PACKAGE
(TOP VIEW)



functional logic diagram (positive logic)



description

The SN75LBC184 and SN65LBC184 are differential data line transceivers in the trade-standard footprint of the SN75176 with built-in protection against high-energy noise transients. This feature provides a substantial increase in reliability for better immunity to noise transients coupled to the data cable over most existing devices. Use of these circuits provides a reliable low-cost direct-coupled (with no isolation transformer) data line interface without requiring any external components.

The SN75LBC184 and SN65LBC184 can withstand overvoltage transients of 400 W peak (typical). The conventional combination wave called out in CEI IEC 1000-4-5 simulates the overvoltage transient and models a unidirectional surge caused by overvoltages from switching and secondary lightning transients.

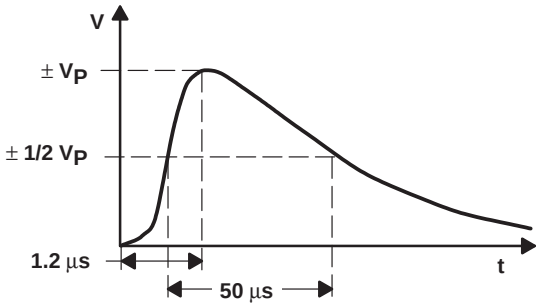


Figure 1. Surge Waveform — Combination Wave

description (continued)

A biexponential function defined by separate rise and fall times for voltage and current simulates the combination wave. The standard 1.2 μs/50 μs combination waveform is shown in Figure 1 and in the test description in Figure 9.

The device also includes additional desirable features for party-line data buses in electrically noisy environment applications including industrial process control. The differential-driver design incorporates slew-rate-controlled outputs sufficient to transmit data up to 250 kbits/s. Slew-rate control allows longer unterminated cable runs and longer stub lengths from the main backbone than possible with uncontrolled and faster voltage transitions. A unique receiver design provides a fail-safe output of a high level when the inputs are left floating (open circuit). The SN75LBC184 and SN65LBC184 receiver also includes a high input resistance equivalent to one-half unit load allowing connection of up to 64 similar devices on the bus.

The SN75LBC184 is characterized for operation from 0°C to 70°C. The SN65LBC184 is characterized from –40°C to 85°C.

DRIVER FUNCTION TABLE

INPUT	ENABLE	OUTPUTS	
D	DE	A	B
H	H	H	L
L	H	L	H
X	L	Z	Z

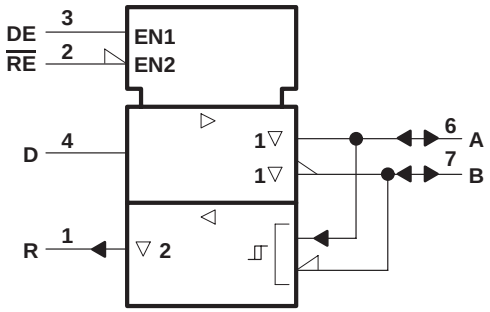
H = high level, L = low level, ? = indeterminate,
X = irrelevant, Z = high impedance (off)

RECEIVER FUNCTION TABLE

DIFFERENTIAL INPUTS	ENABLE	OUTPUT
A – B	RE	R
$V_{ID} \geq 0.2$ V	L	H
-0.2 V < V_{ID} < 0.2 V	L	?
$V_{ID} \leq -0.2$ V	L	L
X	H	Z
Open	L	H

H = high level, L = low level, ? = indeterminate,
X = irrelevant, Z = high impedance (off)

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC} (see Note 1) . . . . . –0.5 V to 7 V
Continuous voltage range at any bus terminal . . . . . –15 V to 15 V
Data input/output voltage . . . . . –0.3 V to 7 V
Electrostatic discharge:
All Terminals (Class 3 A) (see Note 3) . . . . . 8 kV
All Terminals (Class 3 B) (see Note 3) . . . . . 1200 V
Continuous total power dissipation (see Note 2) . . . . . Internally Limited
Operating free-air temperature range, T_A: SN65LBC184 . . . . . –40°C to 85°C
SN75LBC184 . . . . . 0°C to 70°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential input/output bus voltage, are with respect to network ground terminal.
2. The driver shuts down at a junction temperature of approximately 160°C. To operate below this temperature, see the Dissipation Rating Table.
3. GND and bus terminal ESD ratings are beyond readily available test equipment capabilities for MIL-STD-883C method 3015.3.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW
P	1150 mW	9.2 mW/°C	736 mW	598 mW

recommended operating conditions

		MIN	TYP	MAX	UNIT
Supply voltage, V_{CC}		4.75	5	5.25	V
Voltage at any bus terminal (separately or common mode), V_I or V_{IC}		–7‡		12	V
High-level input voltage, V_{IH}	D, DE, and $\overline{RE}$	2			V
Low-level input voltage, V_{IL}	D, DE, and $\overline{RE}$			0.8	V
Differential input voltage, $\lvert V_{ID} \rvert$				12	V
High-level output current, I_{OH}	Driver			–60	mA
	Receiver			–8	mA
Low-level output current, I_{OL}	Driver			60	mA
	Receiver			4	
Operating free-air temperature, T_A	SN75LBC184	0		70	°C
	SN65LBC184	–40‡		85	°C

‡ The algebraic convention, in which the less-positive (more-negative) limit is designated minimum, is used in this data sheet for input voltage, common-mode input voltage, common-mode output voltage, and free-air temperature levels only.

DRIVER SECTION

electrical characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		ALTERNATE SYMBOLS	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
I_{CC}	Supply current	NA	DE = RE = 5 V, No Load	SN75LBC184		12	25	mA
				SN65LBC184		12	30	
			DE = 0 V, RE = 5 V, No Load	SN75LBC184		175	300	µA
				SN65LBC184		175	300	
I_{IH}	High-level input current (D, DE, $\overline{RE}$)	NA	V_I = 2.4 V				±100	µA
I_{IL}	Low-level input current (D, DE, $\overline{RE}$)	NA	V_I = 0.4 V				±100	µA
I_{OS}	Short-circuit output current (see Note 5)	NA	V_O = –7 V			–120	–250	mA
			V_O = V_{CC}				250	
			V_O = 12 V				250	
I_{OZ}	High-impedance output current	NA			See Receiver I_I			mA
V_O	Output voltage	V_{oa}, V_{ob}	I_O= 0‡		0		6	V
$V_{OC(PP)}$	Peak-to-peak change in common-mode output voltage during state transitions	NA	See Figures 5 and 6			0.8		V
V_{OC}	Common-mode output voltage	$\lvert V_{os}\rvert$	See Figure 4		1		3	V
$\lvert\Delta V_{OC(SS)}\rvert$	Magnitude of change, common-mode steady-state output voltage	$\lvert V_{os} - \overline{V}_{os}\rvert$	See Figure 5				0.2	V
$\lvert V_{OD}\rvert$	Magnitude of differential output voltage $\lvert V_A - V_B\rvert$ (see Note 4)	V_o	I_O = 0		1.5		6	V
			R_L = 54 Ω, See Figure 4	$T_A \geq 0°C$	1.5			V
				$T_A < 0°C$	1			V
$\Delta\lvert V_{OD}\rvert$	Change in differential voltage magnitude between logic states	$\lvert\lvert V_t\rvert - \lvert\overline{V}_t\rvert\rvert$	R_L = 54 Ω				0.2	V

† All typical values are measured with T_A = 25°C and V_{CC} = 5 V.
‡ I_O = I_{ia}, I_{ib}. I_{ia} and I_{ib} are alternate symbols for input voltage.

NOTES: 4. The minimum V_{OD} specification of the SN75LBC184 and the SN65LBC184 may not fully comply with ANSI RS-485 at operating temperature below 0°C. System designers should take the possibly lower output signal into account in determining the maximum signal-transmission distance.
5. This parameter is measured with only one output being driven at a time.

DRIVER SECTION (CONTINUED)

switching characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(DH)}$	Differential output delay time, low-to-high-level output	R_L = 54 Ω, C_L = 15 pF See Figure 5			1.5	µs
$t_{d(DL)}$	Differential-output delay time, high-to-low-level output				1.5	µs
t_{PLH}	Propagation delay time, low-to-high-level output			0.5	1.5	µs
t_{PHL}	Propagation delay time, high-to-low-level output			0.5	1.5	µs
$t_{sk(p)}$	Pulse skew ($\lvert t_{d(DH)} - t_{d(DL)} \rvert$)			75	225	ns
t_r	Rise time, single ended	R_L = 54 Ω, C_L = 15 pF, See Figure 5	0.25		1.8	µs
t_f	Fall time, single ended		0.25		1.8	µs
t_{PZH}	Output enable time to high level	R_L = 110 Ω, See Figure 2			3.5	µs
t_{PZL}	Output enable time to low level	R_L = 110 Ω, See Figure 3			3.5	µs
t_{PHZ}	Output disable time from high level	R_L = 110 Ω, See Figure 2			2	µs
t_{PLZ}	Output disable time from low level	R_L = 110 Ω, See Figure 3			2	µs

RECEIVER SECTION

electrical characteristics over recommended operating conditions (unless otherwise noted)

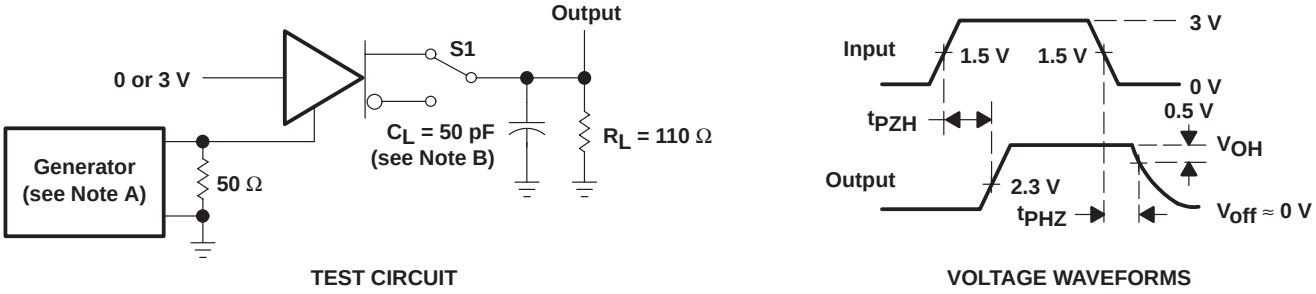
PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
I_{CC}	Supply current (total package)	DE = RE = 0 V, No Load					3.9	mA
		RE = 5 V, DE = 0 V, No Load					300	µA
I_I	Input current	Other input = 0 V	V_I = 12 V				500	µA
			V_I = 12 V,	V_{CC} = 0			500	
			V_I = –7 V				–400	
			V_I = –7 V,	V_{CC} = 0			–400	
I_{OZ}	High-impedance-state output current	V_O = 0.4 V to 2.4 V					±100	µA
V_{hys}	Input hysteresis voltage					70		mV
V_{IT+}	Positive-going input threshold voltage						200	mV
$V_{IT–}$	Negative-going input threshold voltage				–200‡			mV
V_{OH}	High-level output voltage	I_{OH} = –8 mA	Figure 7		2.7			V
V_{OL}	Low-level output voltage	I_{OL} = 4 mA	Figure 7				0.5	V

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ The algebraic convention, in which the less-positive (more-negative) limit is designated minimum, is used in this data sheet for input voltage, common-mode input voltage, common-mode output voltage and free-air temperature levels only.

switching characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	C_L = 50 pF,	See Figure 7			300	ns
t_{PHL}	Propagation delay time, high-to-low-level output					300	ns
$t_{sk(p)}$	Pulse skew ($\lvert t_{pHL} - t_{pLH} \rvert$)					100	ns
t_r	Rise time, single ended	See Figure 7			20		ns
t_f	Fall time, single ended				20		ns
t_{PZH}	Output enable time to high level	See Figure 8				300	ns
t_{PZL}	Output enable time to low level					300	ns
t_{PHZ}	Output disable time from high level					300	ns
t_{PLZ}	Output disable time from low level					300	ns

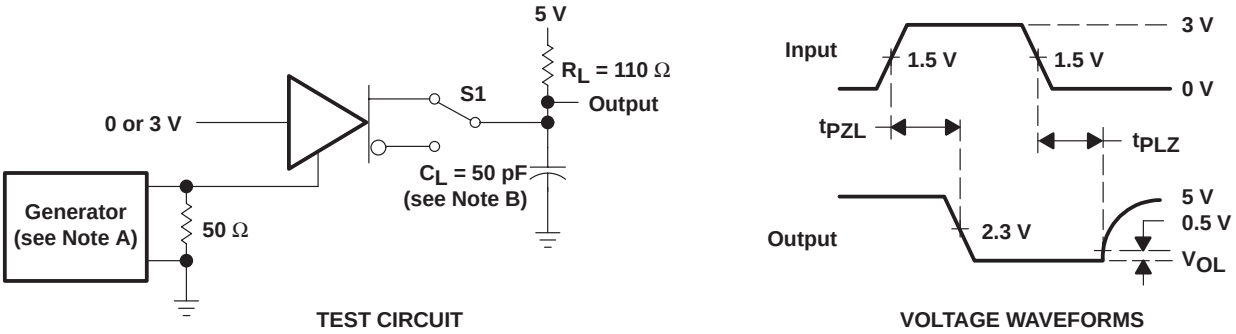
PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT VOLTAGE WAVEFORMS

NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns, $Z_O = 50\ \Omega$.
B. C_L includes probe and jig capacitance.

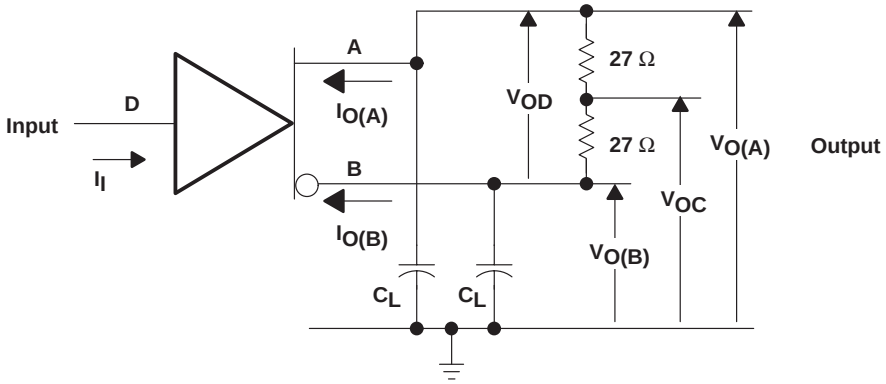
Figure 2. Driver t_{PZH} and t_{PHZ} Test Circuit and Voltage Waveforms



TEST CIRCUIT VOLTAGE WAVEFORMS

NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns, $Z_O = 50\ \Omega$.
B. C_L includes probe and jig capacitance.

Figure 3. Driver t_{PZL} and t_{PLZ} Test Circuit and Voltage Waveforms



NOTES: A. Resistance values are in ohms and are 1% tolerance.
B. C_L includes probe and jig capacitance.

Figure 4. Driver Test Circuit, Voltage, and Current Definitions

PARAMETER MEASUREMENT INFORMATION

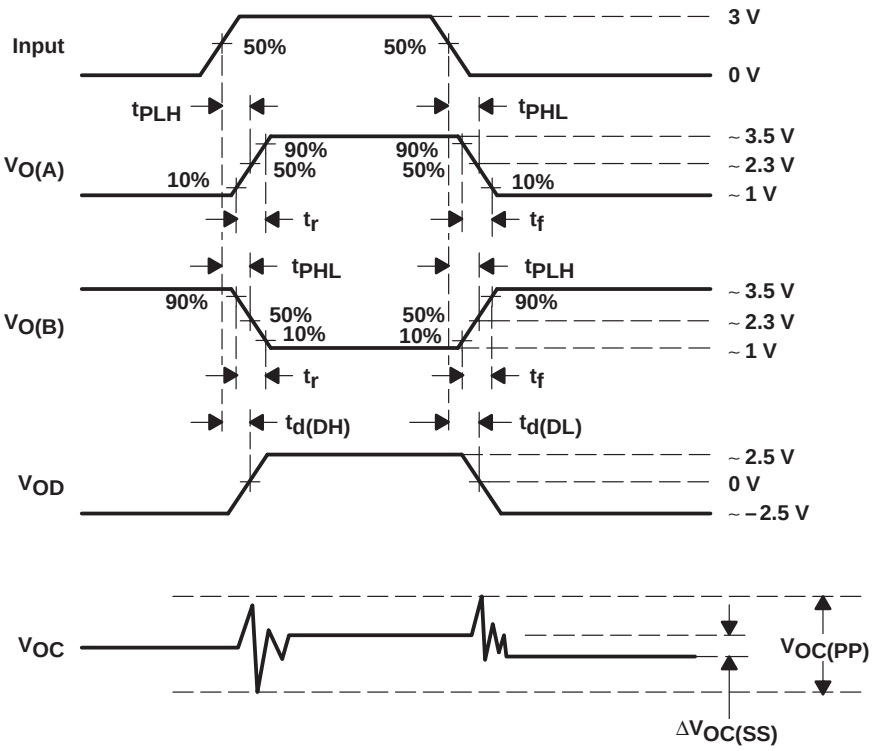
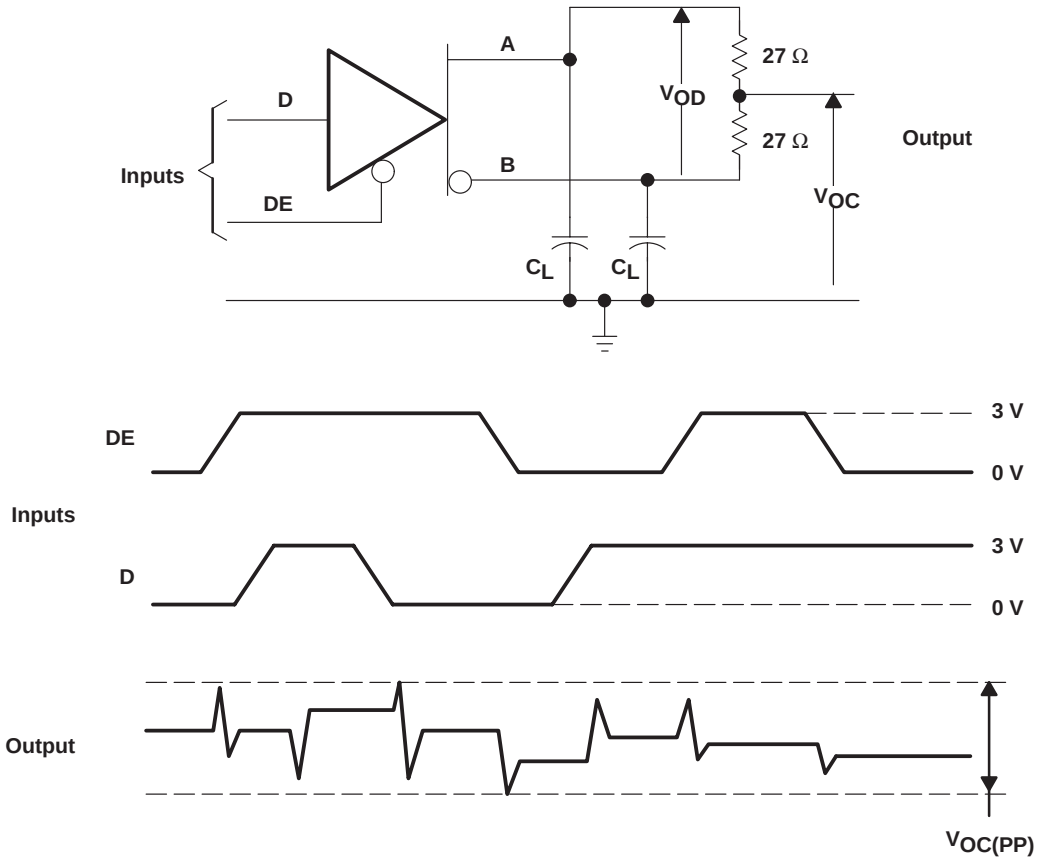


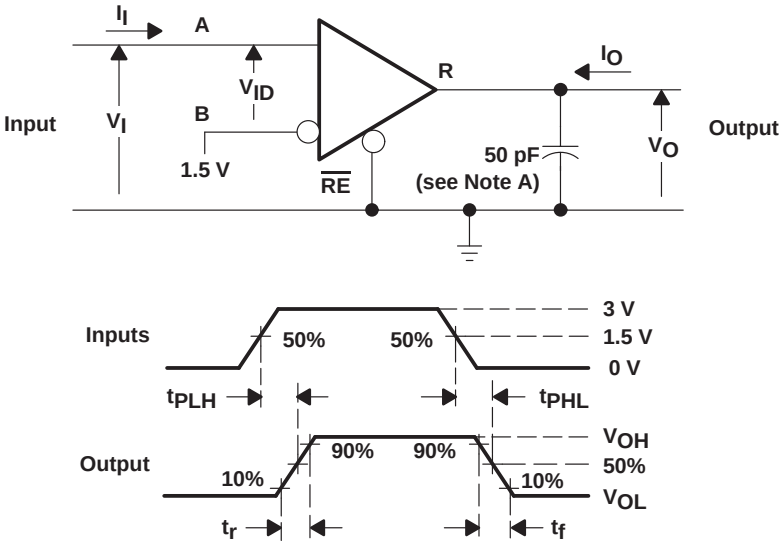
Figure 5. Driver Timing, Voltage and Current Waveforms

PARAMETER MEASUREMENT INFORMATION



NOTES: A. Resistance values are in ohms and are 1% tolerance.
B. C_L includes probe and jig capacitance (± 10%).

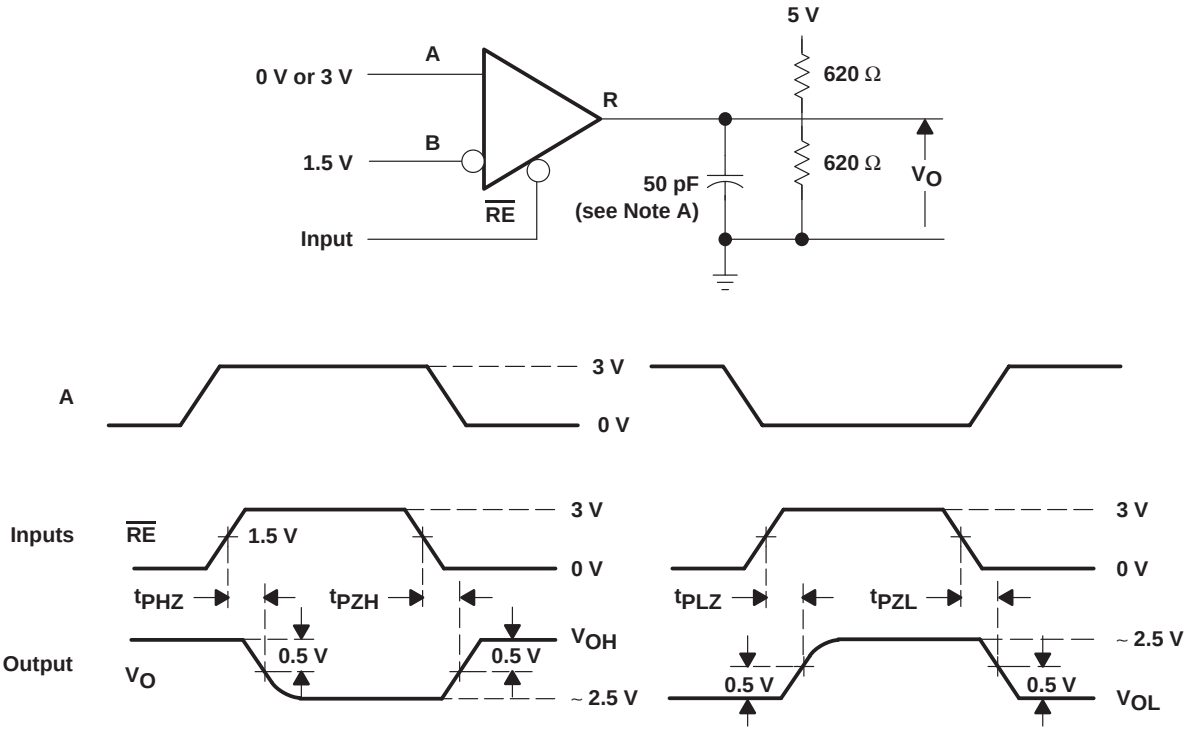
Figure 6. Driver $V_{OC(PP)}$ Test Circuit and Waveforms



NOTE A: This value includes probe and jig capacitance (± 10%).

Figure 7. Receiver t_{PLH} and t_{PHL} Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



NOTE A: This value includes probe and jig capacitance (± 10%).

Figure 8. Receiver t_{PZL}, t_{PLZ}, t_{PZH}, and t_{PHZ} Test Circuit and Voltage Waveforms

APPLICATION INFORMATION

’LBC184 test description

The ’LBC184 is tested against the CEI IEC 1000–4–5 recommended transient identified as the combination wave. The combination wave provides a 1.2-/50-µs open-circuit voltage waveform and a 8-/20-µs short-circuit current waveform shown in Figure 9. The testing is performed with a combination/hybrid pulse generator with an effective output impedance of 2 Ω. The setup for the overvoltage stress is shown in Figure 10 with all testing performed with power applied to the ’LBC184 circuit.

NOTE

High voltage transient testing is done on a sampling basis.

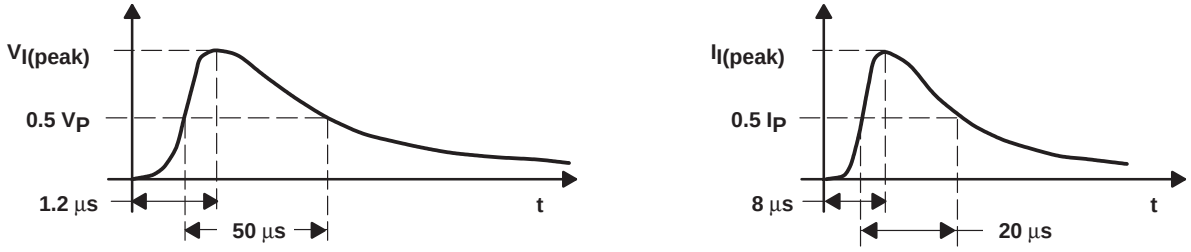


Figure 9. Short-Circuit Current Waveforms

The ’LBC184 is tested and evaluated for both maximum (single pulse) as well as life test (multiple pulse) capabilities. The ’LBC184 is evaluated against transients of both positive and negative polarity and all testing is performed with the worst-case transient polarity. Transient pulses are applied to the bus pins (A & B) across ground as shown in Figure 10.

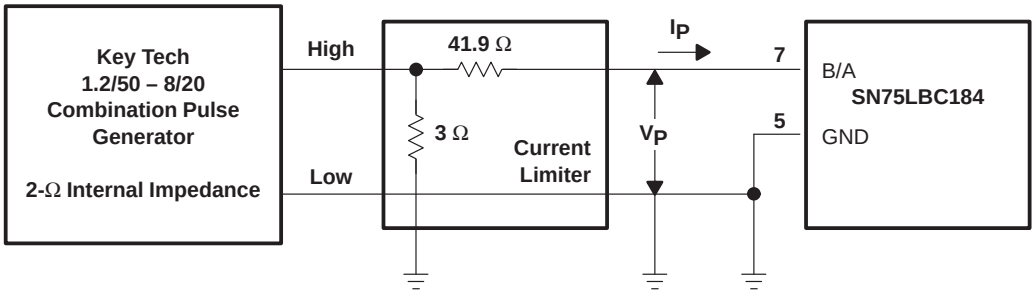


Figure 10. Overvoltage-Stress Test Circuit

An example waveform as seen by the ’LBC184 is shown in Figure 11. The bottom trace is current, the middle trace shows the clamping voltage of the device and the top trace is power as calculated from the voltage and current waveforms. This example shows a peak clamping voltage of 16 V, peak current of 33.6 A yielding an absorbed peak power of 538 W.

NOTE

A circuit reset may be required to ensure normal data communications following a transient noise pulse of greater than 250 W peak.

APPLICATION INFORMATION

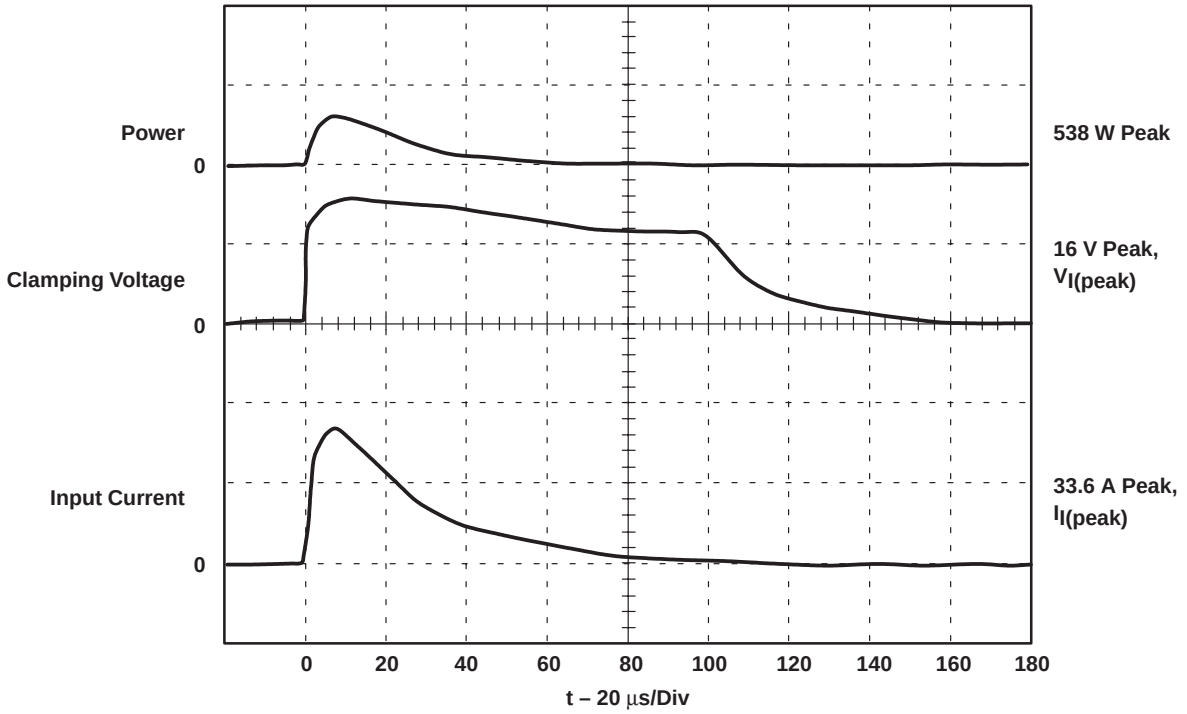
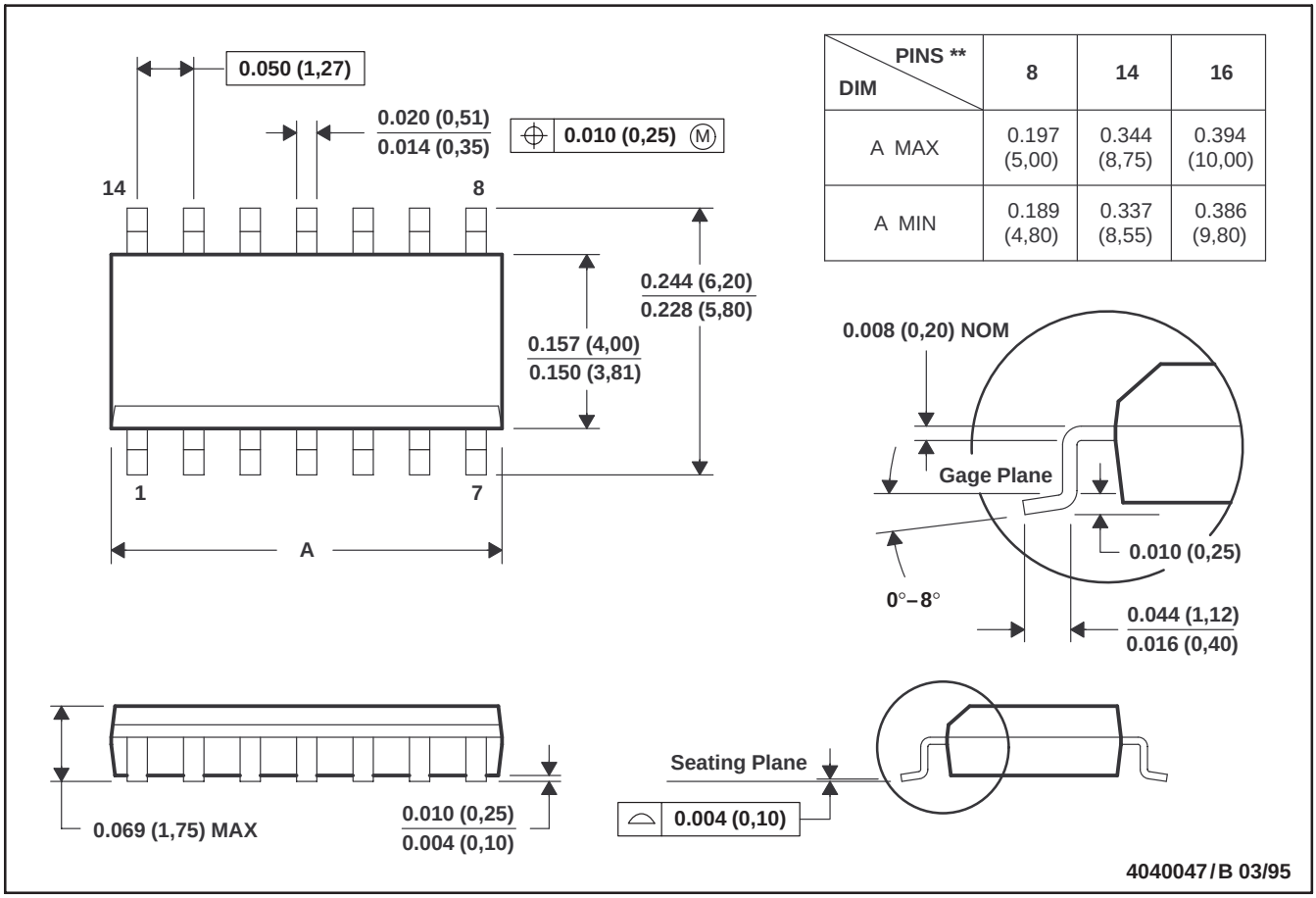


Figure 11. Typical Surge Waveform Measured At Terminals 5 and 7

MECHANICAL INFORMATION

D (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN

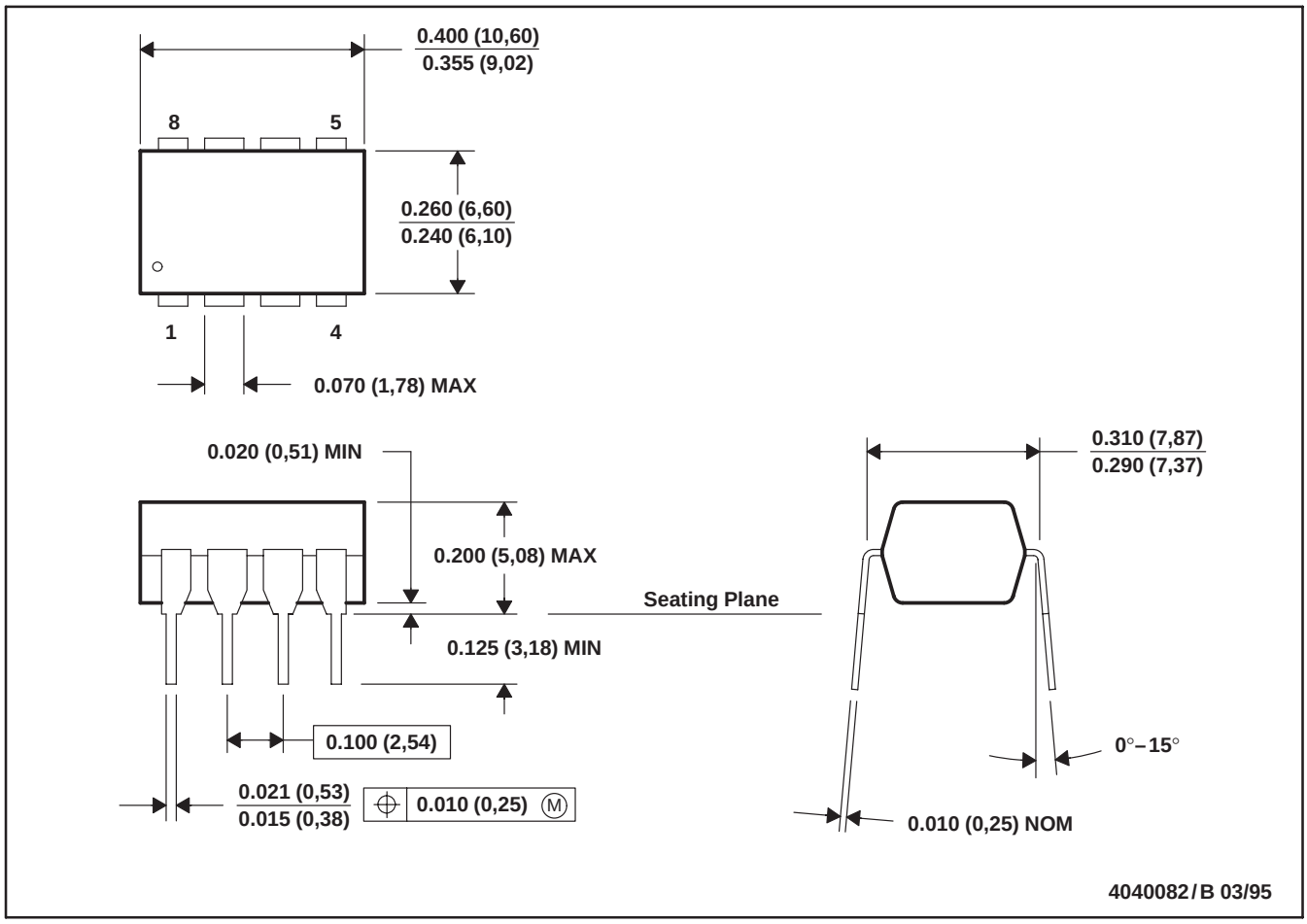


DIM \ PINS **	8	14	16
A MAX	0.197 (5,00)	0.344 (8,75)	0.394 (10,00)
A MIN	0.189 (4,80)	0.337 (8,55)	0.386 (9,80)

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
D. Four center pins are connected to die mount pad.
E. Falls within JEDEC MS-012

MECHANICAL INFORMATION

P (R-PDIP-T8) **PLASTIC DUAL-IN-LINE PACKAGE**



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS-001

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